

Lecture 22 :

<http://www.ee.iitm.ac.in/~nagendra/cadinfo.html>

- 0.18 μ m CMOS process models

Exercise:

$$\left\{ \frac{1.8\mu\text{m}}{0.18\mu\text{m}}, \frac{3.6\mu\text{m}}{0.36\mu\text{m}}, \frac{7.2\mu\text{m}}{0.72\mu\text{m}}, \frac{14.4\mu\text{m}}{1.44\mu\text{m}} \right\}$$

* Plot I_D vs. V_{GS} of nMOS & pMOS transistors
(in saturation region)

* Plot I_D vs. V_{DS} of nMOS & pMOS transistors
(for a range of V_{GS} values - V_{GS} : parameter)

Channel length is very short &

$$I_D = \frac{\mu C_{ox}}{2} \frac{W}{L} (V_{GS} - V_T)^2$$

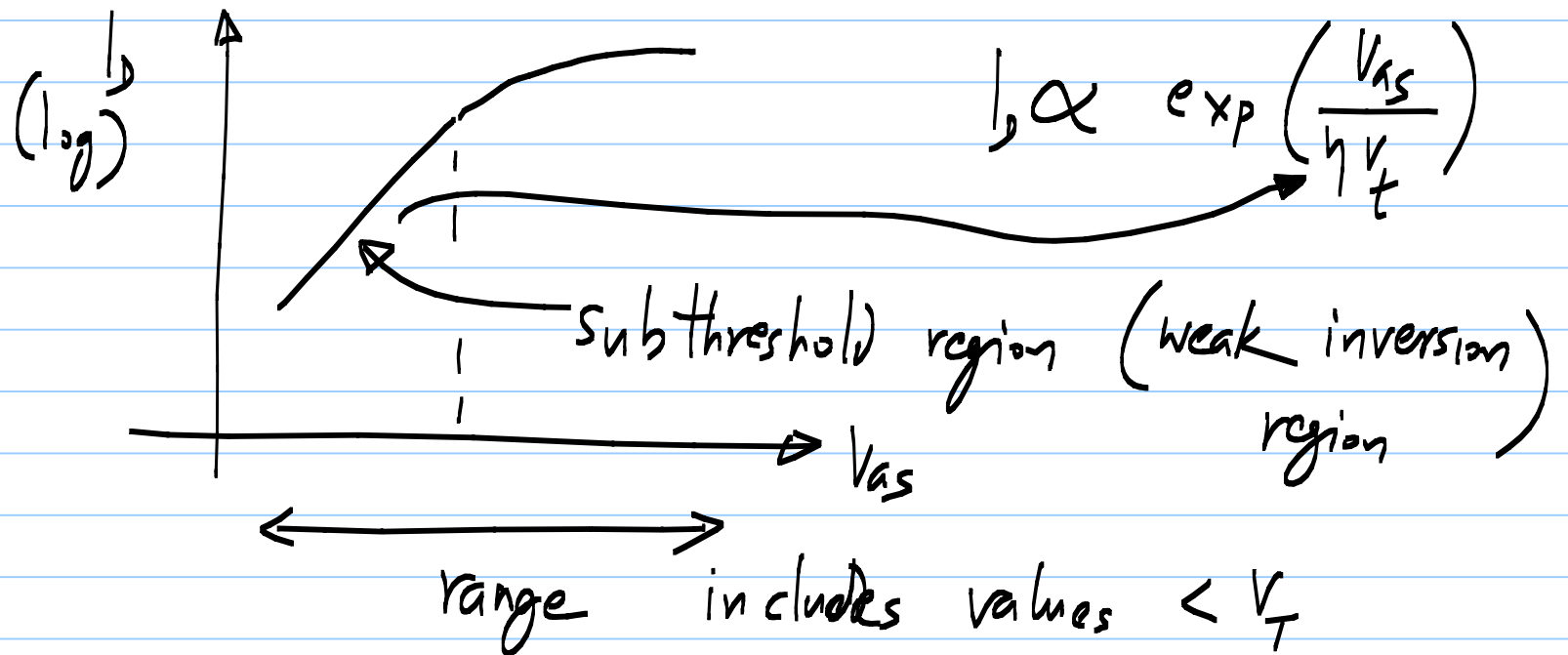
$$\frac{\mu (V_{GS} - V_T)}{L} = v$$

$$= W C_{ox} (V_{GS} - V_T) v_{SAT}$$

↖ saturation velocity

Current in sub threshold region.

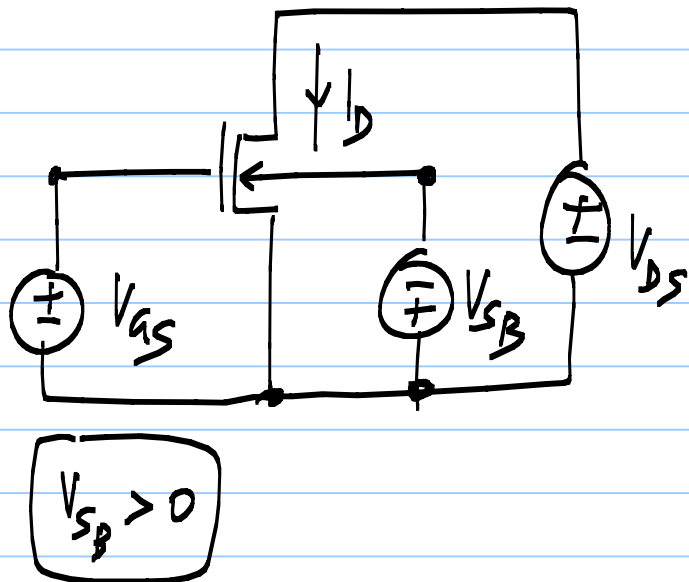
* Plot I_D vs. V_{GS} (on a log scale).



* Find the effect of V_{SB}

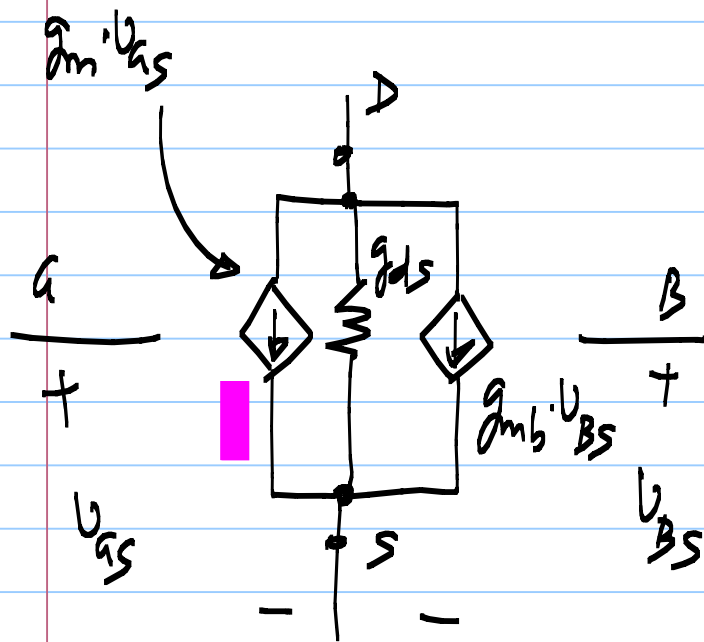
* Plot I_D vs. V_{SB}

(V_{DS}, V_{GS} : strong inversion & saturation)



* Plot I_D vs. V_{DS} for different values of V_{SB}
(V_{SB} : parameter)

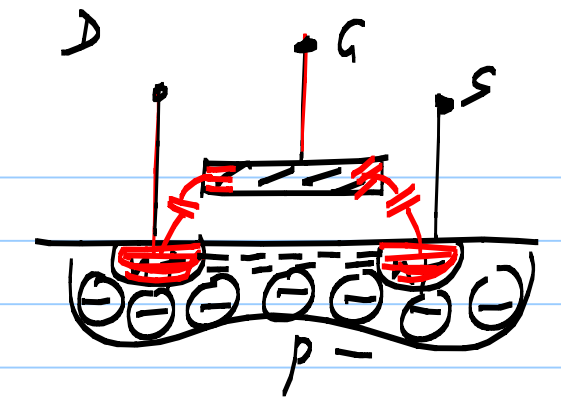
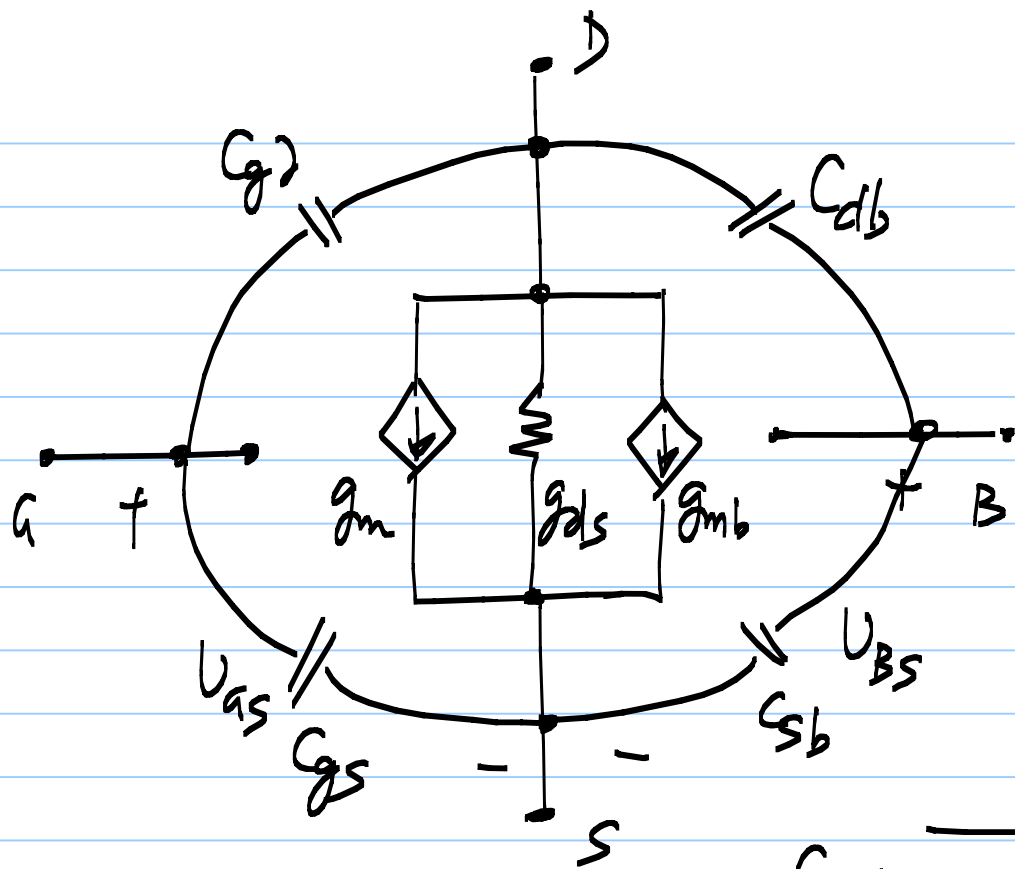
dc Small signal model of the MOS transistor:



$$I_D = f(V_{GS}, V_{DS}, V_{BS})$$

$$\Delta I_D = \left. \frac{\partial I_D}{\partial V_{GS}} \right|_{V_{DS}, V_{BS}} v_{gs} + \left. \frac{\partial I_D}{\partial V_{DS}} \right|_{V_{GS}, V_{BS}} v_{ds} + \left. \frac{\partial I_D}{\partial V_{BS}} \right|_{V_{GS}, V_{DS}} v_{BS}$$

The partial derivatives in the equation above are highlighted with colored boxes: $\left. \frac{\partial I_D}{\partial V_{GS}} \right|_{V_{DS}, V_{BS}}$ is in a pink box, $\left. \frac{\partial I_D}{\partial V_{DS}} \right|_{V_{GS}, V_{BS}}$ is in a cyan box, and $\left. \frac{\partial I_D}{\partial V_{BS}} \right|_{V_{GS}, V_{DS}}$ is in a cyan box. Red arrows point from these boxes to the labels g_m , g_{ds} , and g_{mb} respectively.

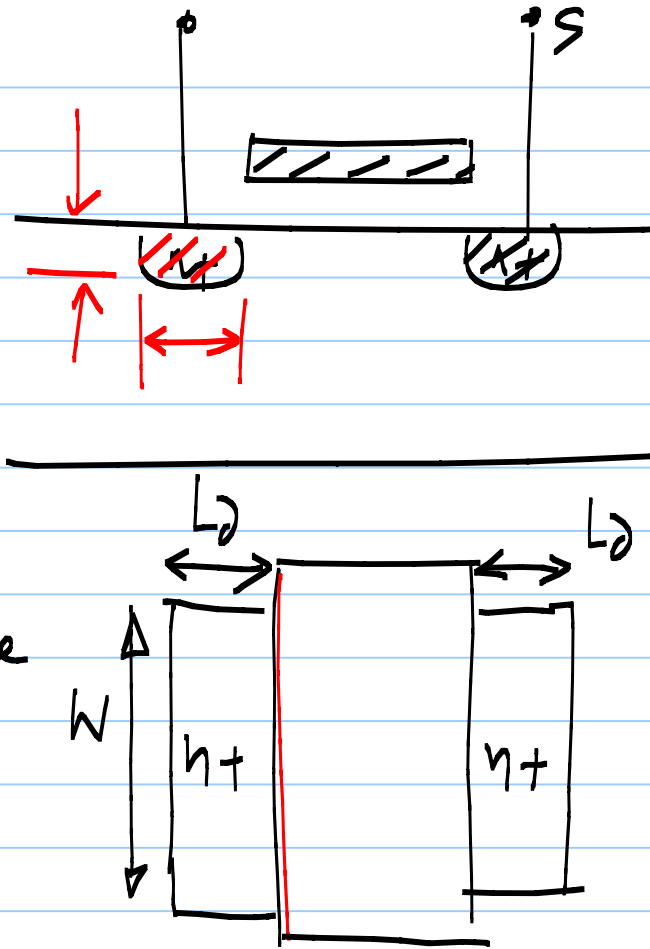


C_{gd}, C_{gs} : intrinsic capacitances

	Triode	Saturation
C_{gd}	$\frac{1}{2} \cdot W \cdot L \cdot C_{ox}$	$0 + C_{ov}' \cdot W$
C_{gs}	$\frac{1}{2} W L C_{ox}$	$\frac{2}{3} W L C_{ox} + C_{ov}' \cdot W$

C_{sb}, C_{db} :

Area capacitance
+
perimeter capacitance



$$\underline{L_d = 2 \cdot L_{min}}$$

$$C_{sb} = W \cdot L_g \cdot C_{area} (A_s)$$

$$+ \underbrace{2(W + L_d)}_{(P_s)} \cdot C_{perim}$$

$$C_{db} = A_d \cdot C_{area} + P_d \cdot C_{peri}$$

Small signal model:

$$\text{dc} \left\{ \begin{array}{l} g_m = \frac{2I_D}{V_{GS} - V_T} \quad (\text{strong inv.}) ; \frac{I_D}{\eta V_T} \quad (\text{weak inv.}) \\ g_{ds} = \lambda \cdot I_D \\ g_{mb} = g_m \cdot \frac{\partial V_T}{\partial V_{SB}} \end{array} \right.$$

$$\text{Capacitances} \left\{ \begin{array}{l} C_{gd} = 0 + C_{ov}' \cdot W \\ C_{gs} = \frac{2}{3} C_{ox} WL + C_{ov}' \cdot W \\ C_{sb} = A_s \cdot C_{j,area} + P_s \cdot C_{j,peri} \\ C_{db} = A_d \cdot C_{j,area} + P_d \cdot C_{j,peri} \end{array} \right.$$

$$I_D = \frac{\mu_n C_{ox}}{2} \cdot \frac{W}{L} (V_{GS} - V_T)^2 (1 + \lambda V_{DS})$$

$$g_m = \frac{\partial I_D}{\partial V_{GS}} = \mu_n C_{ox} \cdot \frac{W}{L} (V_{GS} - V_T) (1 + \lambda V_{DS})$$

$$= \mu_n C_{ox} \frac{W}{L} (V_{GS} - V_T)$$

$$= \frac{2 \cdot I_D}{V_{GS} - V_T}$$

$$= \sqrt{2 \cdot \mu_n C_{ox} \frac{W}{L} \cdot I_D}$$

$$g_m = \frac{2I_D}{V_{GS} - V_T}$$

Square law model
is valid.

$$V_{GS} - V_T > 6 \cdot V_t$$

(thermal voltage)

$$\approx 150\text{mV}$$

Subthreshold region

$$I_D = I_0 \cdot \exp\left(\frac{V_{GS}}{\eta \cdot V_t}\right)$$

$$\frac{\partial I_D}{\partial V_{GS}} = \frac{I_D}{\eta V_t}$$

$$g_{m_s} = \frac{\partial I_D}{\partial V_{DS}} = \underbrace{\frac{\mu C_{ox}}{2} \frac{W}{L} (V_{GS} - V_T)^2}_{\lambda I_D} \lambda$$

$$= \underline{\underline{\lambda I_D}}$$

$$g_{m_b} = \frac{\partial I_D}{\partial V_{BS}} = \frac{\partial I_D}{\partial V_T} \cdot \frac{\partial V_T}{\partial V_{BS}} = + \mu C_{ox} \frac{W}{L} (V_{GS} - V_T) (1 + \lambda V_{DS})$$

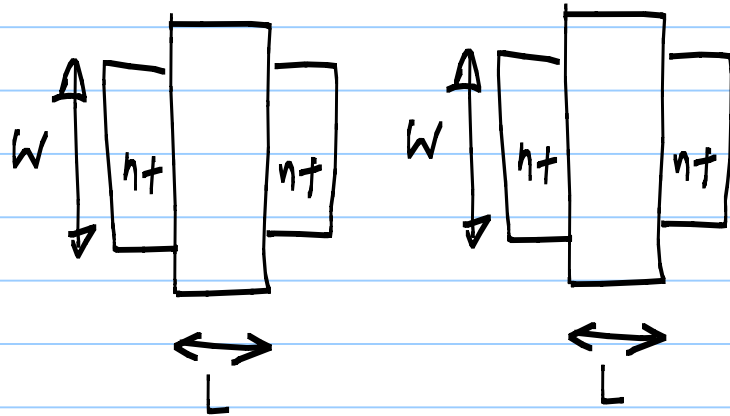
$$= \underline{\underline{g_m \left(\frac{\partial V_T}{\partial V_{SB}} \right)}}$$

$$\frac{\partial V_T}{\partial V_{SB}} = \frac{1}{2} \dots \frac{1}{4}$$

MOS transistor mismatch:

For a given V_{GS} , V_{DS} , V_{SB}

same current



$$I_D = \left\{ \frac{\mu C_{ox}}{2} \frac{W}{L} \right\} (V_{GS} - V_T)^2$$

$$= \frac{\beta}{2} (V_{GS} - V_T)^2$$

V_T mismatch:

$$\sigma_{V_T} = \sigma(V_{T1} - V_{T2}) = \frac{A_{V_T}}{\sqrt{WL}}$$

{mV}

β mismatch:

$$\sigma_{\beta} = \sigma\left(\frac{\beta_1 - \beta_2}{\beta_0}\right) = \frac{A_{\beta}}{\sqrt{WL}}$$

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